

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5347-208		Serial No. 09/891,552	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Gerald Lucovsky et al.			
				Filing Date: June 25, 2001		GAU: 2814	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
		Wilk et al., <i>High-K Gate Dielectrics: Current Status and Materials Properties Considerations</i> , Journal of Applied Physics, Vol. 89, No. 10, May 15, 2001, pp. 5243-5275					
		Lucovsky et al., <i>Microscopic Model for Enhanced Dielectric Constants in Low Concentration SiO₂-Rich Noncrystalline Zr and Hf Silicate Alloys</i> , Applied Physics Letters, Vol. 77, No. 18, October 30, 2000, pp. 2912-2914					
	3	Buchanan et al., <i>80 nm Poly-Silicon Gated n-FETs with Ultra-Thin Al₂O₃ Gate Dielectric for ULSI Applications</i> , IEDM, 2000, pp. 223-226					
	4	Robertson et al., <i>Band Offsets of Wide-Band-Gap Oxides and Implications for Future Electronic Devices</i> , J. Vac. Sci. Technol. B, Vol. 18, No. 3, May/June 2000, pp. 1785-1791					
	5	Gusev et al., <i>High-Resolution Depth Profiling in Ultrathin Al₂O₃ Films on Si</i> , Applied Physics Letters, Vol. 76, No. 2, January 10, 2000, pp. 176-178					
	6	Chin et al., <i>High Quality La₂O₃ and Al₂O₃ Gate Dielectrics With Equivalent Oxide Thickness 5-10Å</i> , 2000 IEEE Symposium on VLSI Technology, Digest of Technical Papers, pp. 16-17					
	7	Klein et al., <i>Evidence of Aluminum Silicate Formation During Chemical Vapor Deposition of Amorphous Al₂O₃ Thin Films on Si(100)</i> , Applied Physics Letters, Vol. 75, No. 25, December 20, 1999, pp. 4001-4003					
	8	Lucovsky, U.S. Serial No. 09/434,607, filed November 5, 1999					
	9	International Technology Roadmap for Semiconductors, 1999 Edition					
	10	Baumvol, <i>Atomic Transport During Growth of Ultrathin Dielectrics on Silicon</i> , Surface Science Reports, Vol. 36, pp. 1-166					
	11	Hinds et al., <i>Investigation of Postoxidation Thermal Treatments of Si/SiO₂ Interface in Relationship to the Kinetics of Amorphous Si Suboxide Decomposition</i> , J. Vac. Sci. Technol. B, Vol. 16, No. 4, July/August 1998, pp. 2171-2176					
	12	Yasuda et al., <i>Low-Temperature Formation of Device-Quality SiO₂/Si Interfaces by a Two-Step Remote Plasma-Assisted Oxidation/Deposition Process</i> , J. Vac. Sci. Technol. B, Vol. 10, No. 4, July/August 1992, pp. 1844-1851					
	13	Hersee et al., <i>The Operation of Metalorganic Bubblers at Reduced Pressure</i> , J. Vac. Sci. Technol. A, Vol. 8, No. 2, March/April 1990, pp. 800-804					
	14	Hunt et al., <i>The Absolute Determination of Resonant Energies for the Radiative Capture of Protons by Boron, Carbon, Fluorine, Magnesium, and Aluminum in the Energy Range Below 500 kev</i> , Physical Review, Vol. 89, No. 6, March 15, 1953, pp. 1283-1287					

Examiner: _____ Date Considered: _____

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

